

# BRCS070P03BD

Rev.A May.-2024

## 描述 / Descriptions

TO-263 塑封封装 P 沟道场效应管。  
P-CHANNEL MOSFET in a TO-263 Plastic Package.

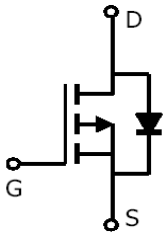
## 特征 / Features

$V_{DS} = -30V$   $I_D = -98A$   
 $R_{DS(on)} @ -10V \leq 7.0m\Omega$  (Type.6.7m $\Omega$ )  
 $R_{DS(on)} @ -4.5V \leq 15m\Omega$  (Type.9.0m $\Omega$ )  
 无卤产品。HF Product.

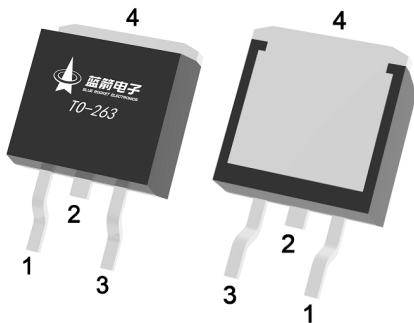
## 用途 / Applications

高频开关和同步整流、BMS、电机。  
High frequency switching and synchronous rectification, BMS, Motor.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN 1 : G    PIN 2、4 : D    PIN 3 : S

## 印章代码 / Marking

见印章说明。  
See Marking Instructions.

**极限参数 / Absolute Maximum Ratings( $T_a=25^{\circ}\text{C}$ )**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Drain Current - Continuous	$I_D(T_c=25^{\circ}\text{C})$	-98	A
Drain Current – Pulsed	$I_{DM}$	-310	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D(T_c=25^{\circ}\text{C})$	100	W
Single Pulse Avalanche Energy(L=0.5mH)	$E_{AS}$	360	mJ
Avalanche Current(L=0.5mH)	$I_{AS}$	30	A
Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^{\circ}\text{C}$
Thermal resistance, junction - ambient	Steady-State $R_{\theta JA}$	65	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction - case	Steady-State $R_{\theta JC}$	1.25	

**电性能参数 / Electrical Characteristics( $T_a=25^{\circ}\text{C}$ )**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=-250\mu\text{A}$ $V_{GS}=0\text{V}$	-30	-34		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30\text{V}$ $V_{GS}=0\text{V}$			-1	$\mu\text{A}$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu\text{A}$	-1	-1.4	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10\text{V}$ , $I_D=-20\text{A}$		6.7	7	m $\Omega$
		$V_{GS}=-4.5\text{V}$ , $I_D=-10\text{A}$		9.0	15	
Diode Forward Voltage	$V_{SD}$	$I_S=-1\text{A}$ , $V_{GS}=0\text{V}$			-1.2	V
Input Capacitance	$C_{iss}$	$V_{DS}=-25\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		3260		pF
Output Capacitance	$C_{oss}$			335		
Reverse Transfer Capacitance	$C_{rss}$			330		
Gate resistance	$R_g$	$V_{GS}=0\text{V}$ $V_{DS}=0\text{V}$ $f=1\text{MHz}$		5.6		$\Omega$
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $I_D=-20\text{A}$		51		nC
Total Gate Charge	$Q_{g(4.5V)}$			32		
Gate Source Charge	$Q_{gs}$			11		
Gate Drain Charge	$Q_{gd}$			13		

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-15V$ $R_L=0.75\Omega$ $R_{GEN}=3\Omega$		12.5		ns
Turn-On Rise Time	$t_r$			19		
Turn-Off Delay Time	$t_{d(off)}$			125		
Turn-Off Fall Time	$t_f$			67		

## 电参数曲线图 / Electrical Characteristic Curve

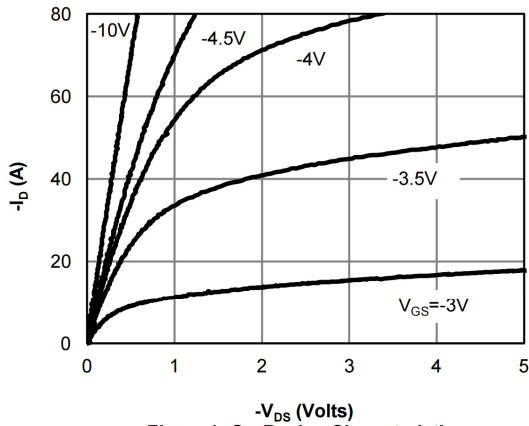


Figure 1: On-Region Characteristics

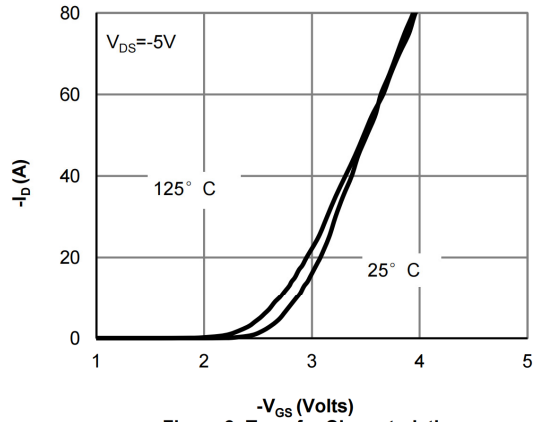


Figure 2: Transfer Characteristics

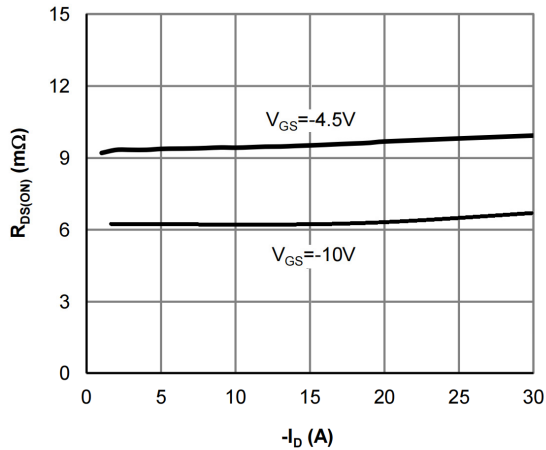


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

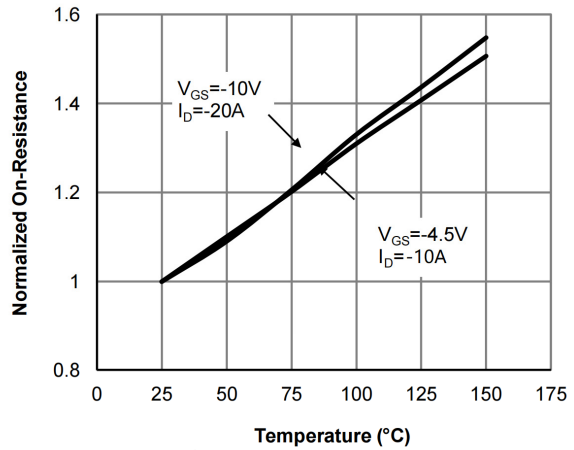


Figure 4: On-Resistance vs. Junction Temperature

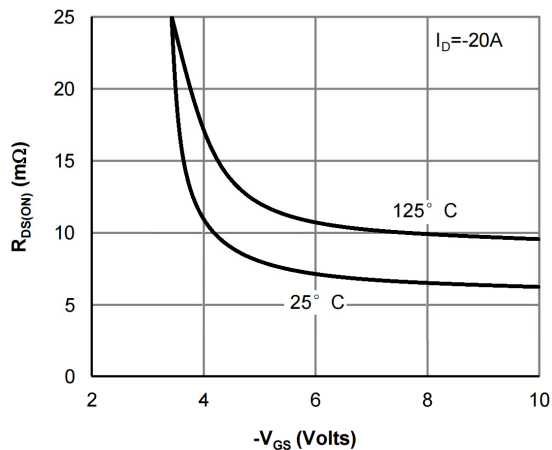


Figure 5: On-Resistance vs. Gate-Source Voltage

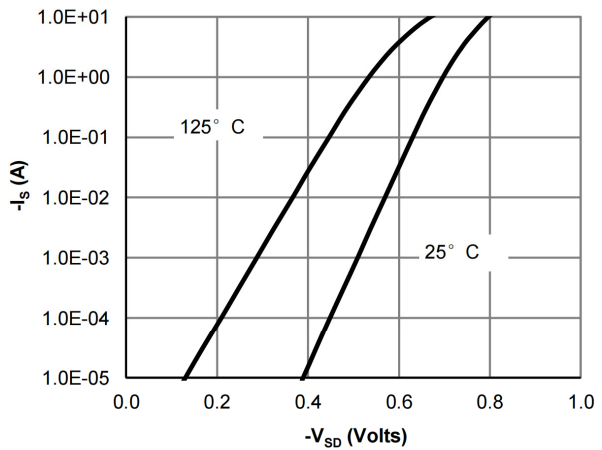


Figure 6: Body-Diode Characteristics

## 电参数曲线图 / Electrical Characteristic Curve

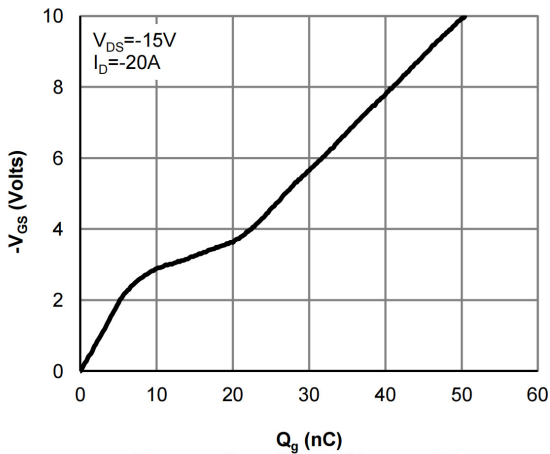


Figure 7: Gate-Charge Characteristics

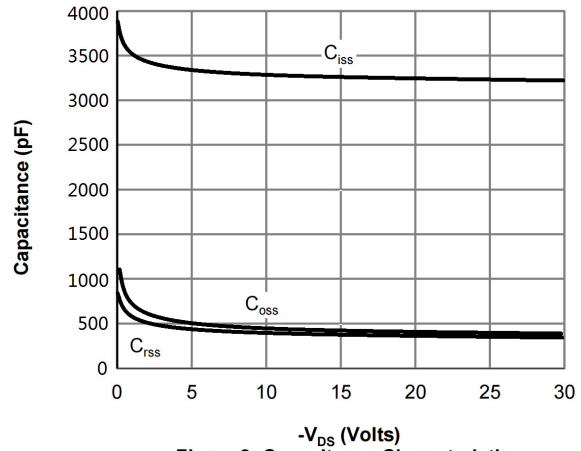


Figure 8: Capacitance Characteristics

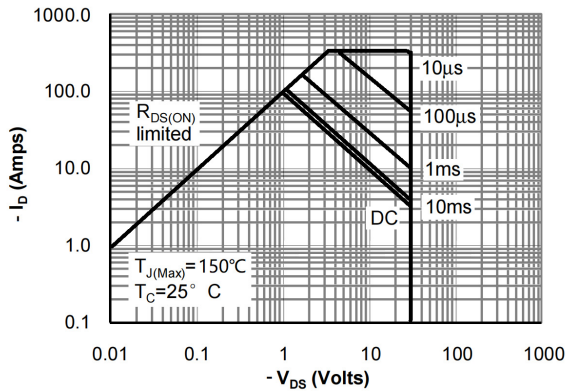


Figure 9: Maximum Forward Biased Safe Operating Area

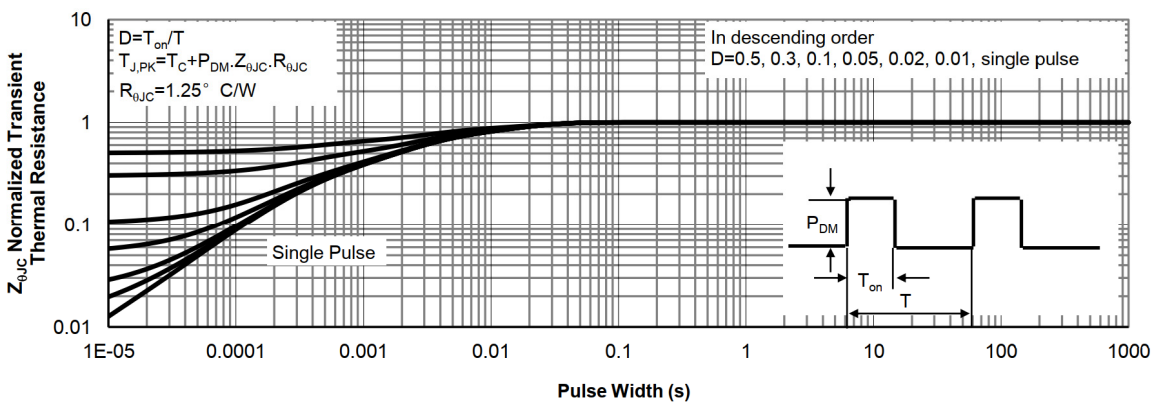
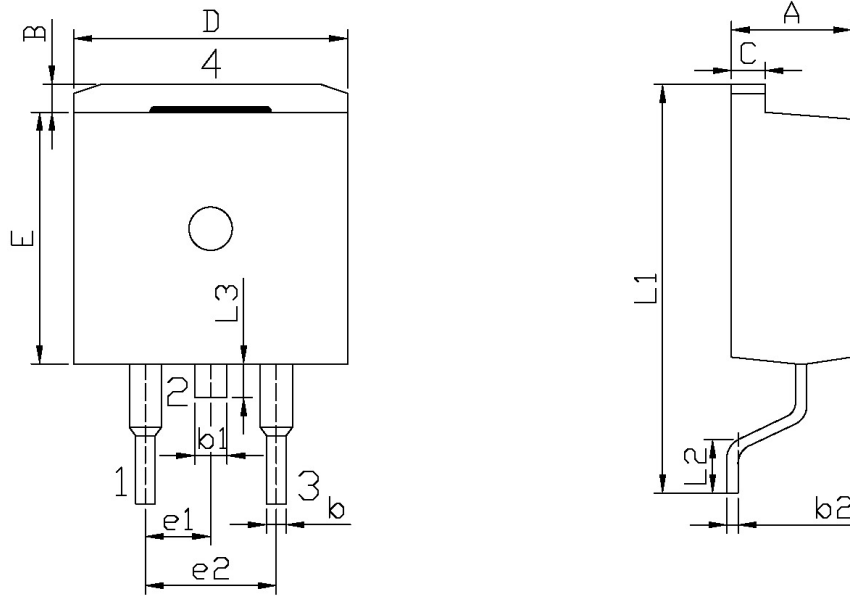


Figure 10: Normalized Maximum Transient Thermal Impedance

**外形尺寸图 / Package Dimensions**

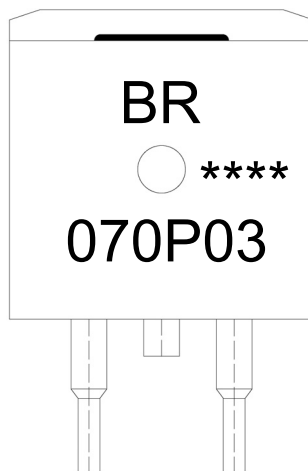


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74
b	0.70	0.90	e2	4.88	5.28
b1	1.15	1.35	L1	15.00	16.00
b2	0.40	0.60	L2	2.24	2.84
C	1.20	1.40	L3	1.20	1.60
D	9.80	10.20			

TQ-263

## 印章说明 / Marking Instructions



说明：

BR： 为公司代码

070P03： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

070P03: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-263	800	1	800	6	4,800	13" ×24	360×360×50	380×335×366

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

**使用说明 / Notices**